

PSMN016-100BS

N-channel 100V 16 m Ω standard level MOSFET in D2PAK Rev. 2 — 1 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK packages qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$T_j = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{}$	-	-	57	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	148	W
Tj	junction temperature		-55	-	175	°C
Static characte	eristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C}; \text{see}$ Figure 12	-	-	28.8	mΩ
		V_{GS} = 10 V; I_{D} = 15 A; T_{j} = 25 °C; see <u>Figure 13</u>	-	13	16	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A}; V_{DS} = 50 \text{ V};$	-	15	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	49	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	-	101	mJ



2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
	S	source	i	
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN016-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 ^{\circ}\text{C}; T_j \ge 25 ^{\circ}\text{C}; R_{GS} = 20 \text{k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	40	Α
		$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	57	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	230	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	148	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drain of	diode				
Is	source current	$T_{mb} = 25 ^{\circ}C$	-	57	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	230	Α
Avalanche rug	gedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	101	mJ

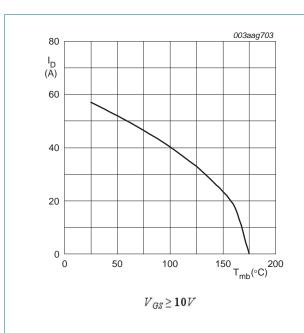


Fig 1. Continuous drain current as a function of mounting base temperature

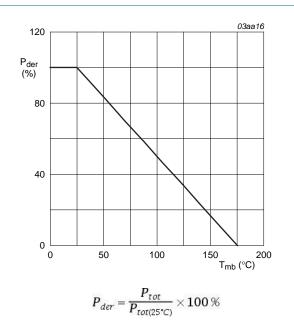
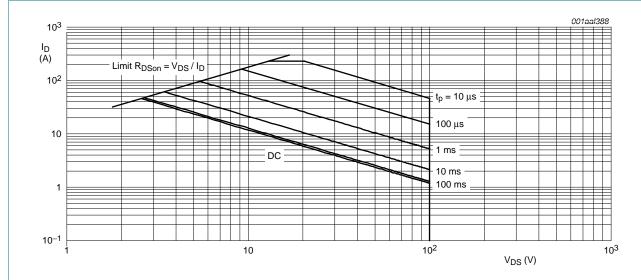


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.56	1.01	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		<u>[1]</u> _	50	-	K/W

[1] minimum footprint; mounted on a printed-circuit board to ambient

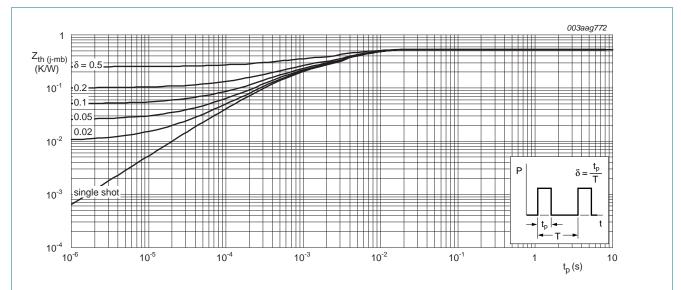


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.8	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 15 \text{ A; } T_j = 100 \text{ °C;}$ see Figure 12	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	36.4	44.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 10 V$; see Figure 14	-	40	-	nC
		$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	49	-	nC
Q _{GS}	gate-source charge	see Figure 14;see Figure 15	-	12	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	7.75	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.25	-	nC
Q_{GD}	gate-drain charge	$I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ;see <u>Figure 15</u>	-	15	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.5	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2404	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	189	-	pF
C _{rss}	reverse transfer capacitance		-	113	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.7 \Omega; V_{GS} = 10 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 ^{\circ}C$	-	23	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	18	-	ns

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Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	54	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}$	-	126	-	nC

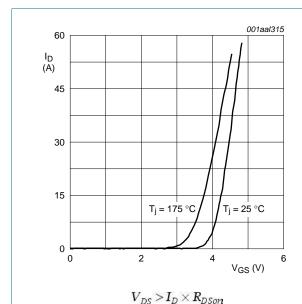


Fig 5. Transfer Characteristic: drain current as a function of gate-source voltage; typical values

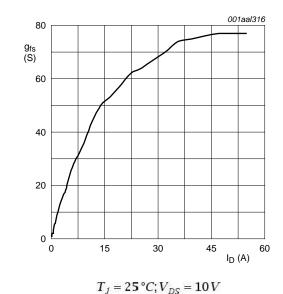


Fig 6. forward transconductance as a function of drain current; typical values

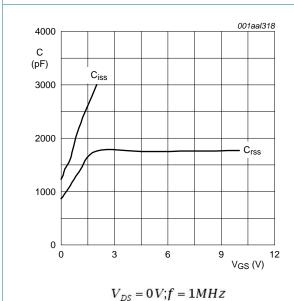
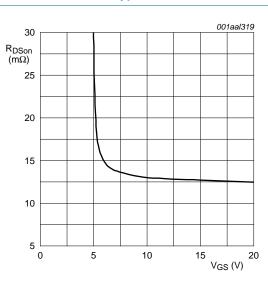


Fig 7. Input and revers transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25\,^{\circ}C; I_D = 5A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

PSMN016-100BS

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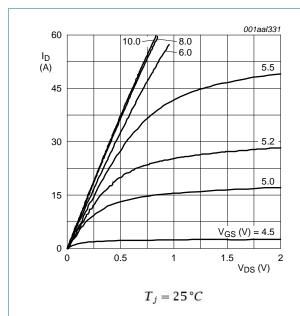


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

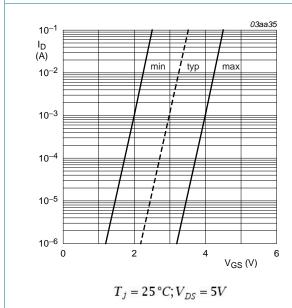
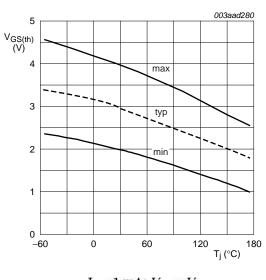


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

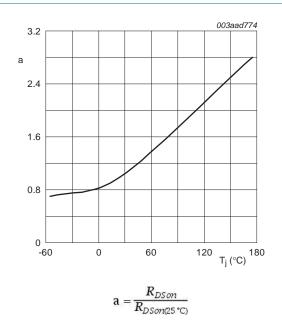
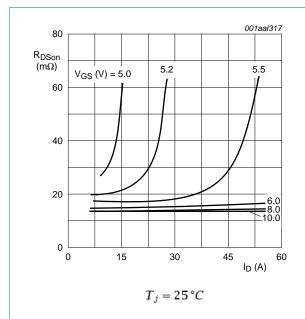


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V_{GS}(pl)

V_{GS}(th)

V_{GS}

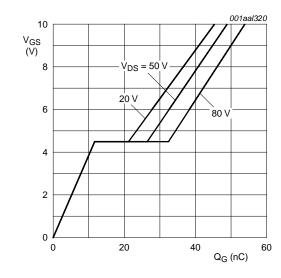
Q_{GS1}
Q_{GS2}

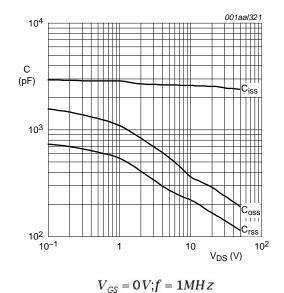
Q_{GS}
Q_G(tot)

003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values







 $T_j = 25 \,^{\circ}C; I_D = 30A$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

Fig 15. Gate-source voltage as a function of gate charge; typical values

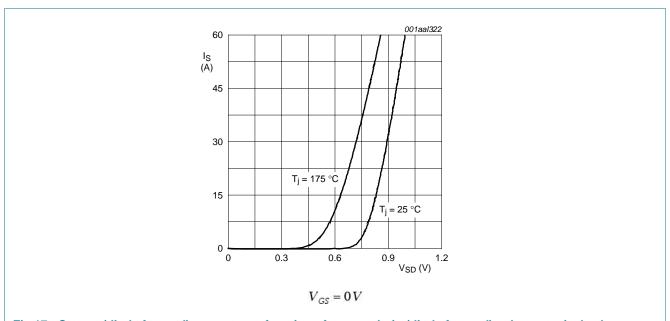


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

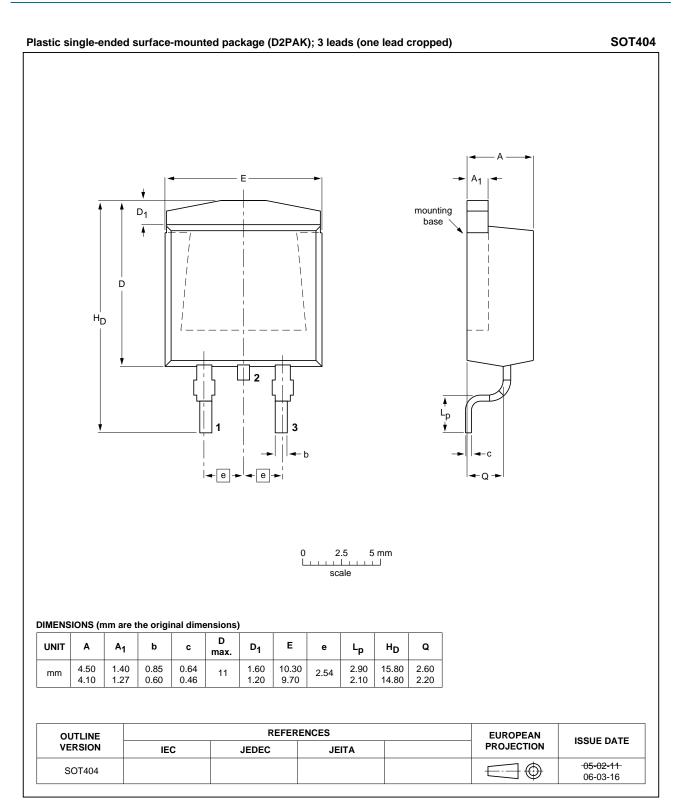


Fig 18. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100BS v.2	20120301	Product data sheet	-	PSMN016-100BS v.1
Modifications:	 Status changed from 	om objective to product.		
	 Various changes to 	content.		
PSMN016-100BS v.1	20111025	Objective data sheet	-	-

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9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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